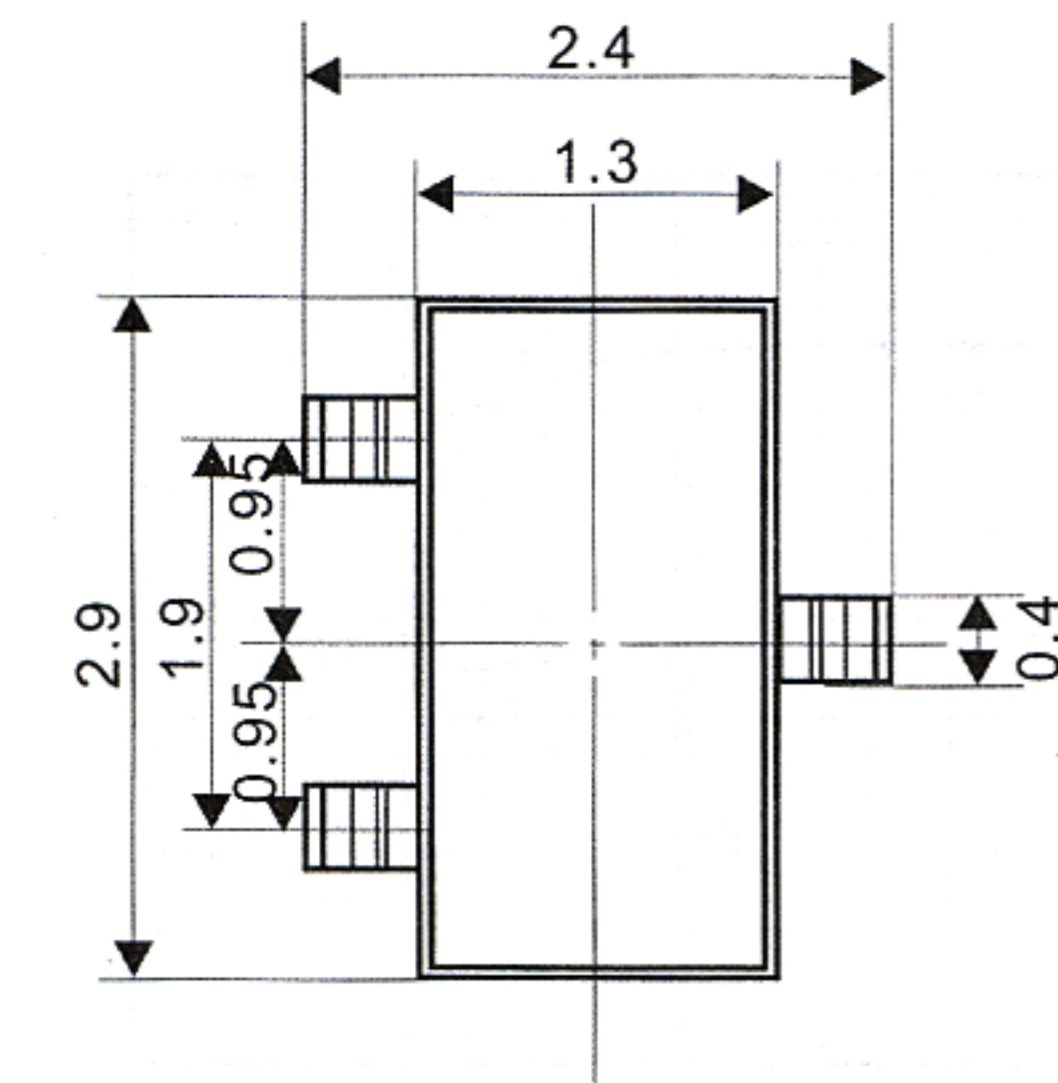
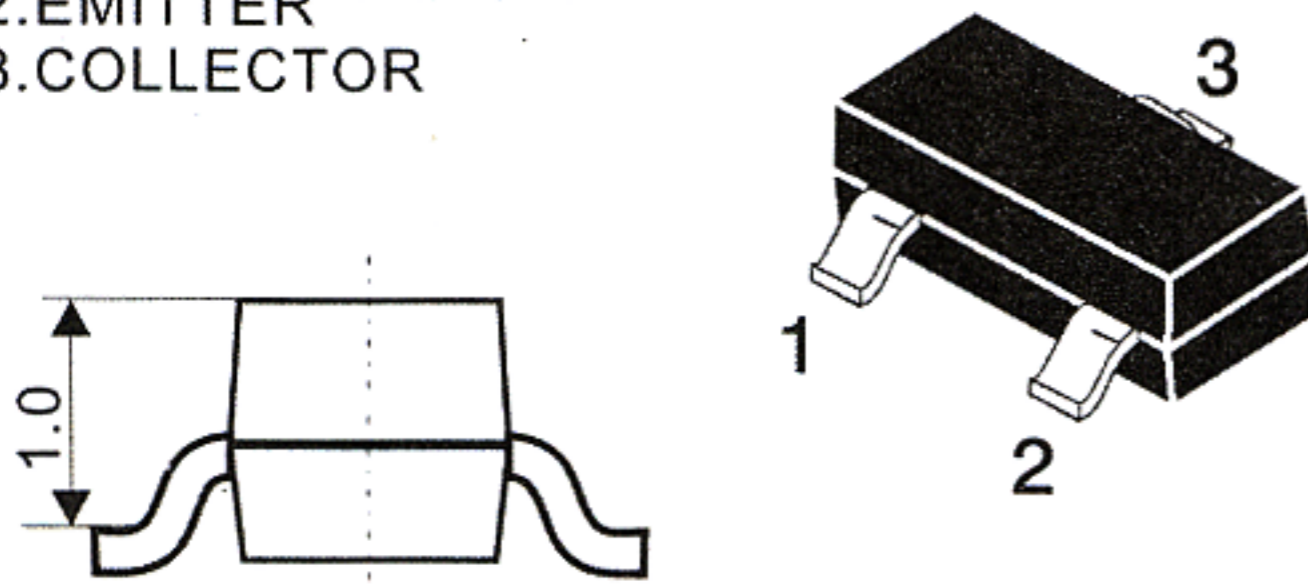


SOT-23 Plastic-Encapsulate Transistors

S9015LT1 TRANSISTOR (PNP)

- 1.BASE
- 2.EMITTER
- 3.COLLECTOR



UNIT: mm

FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -50V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

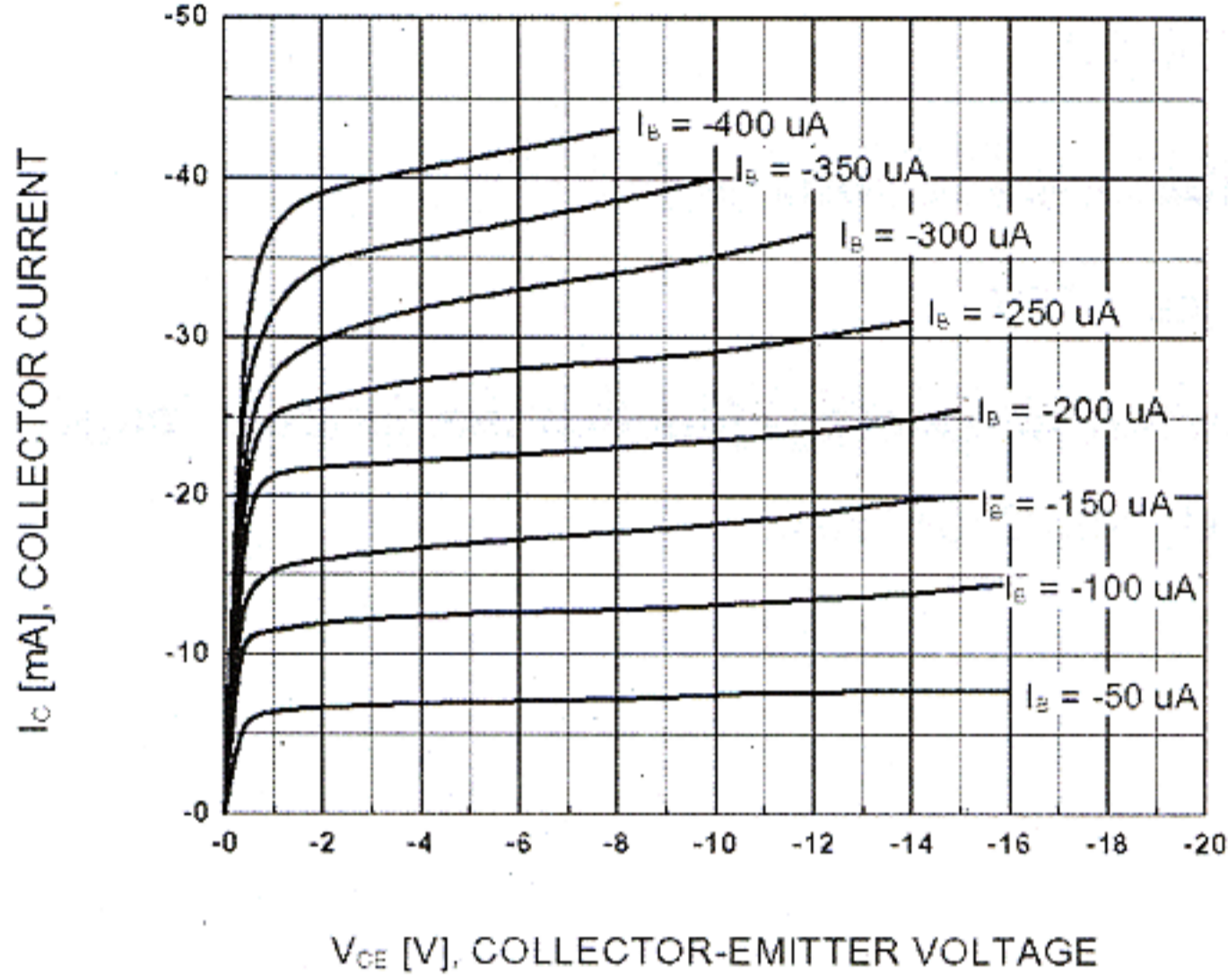
($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5		-0.05	V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			1000	μA
DC current gain	h_{FE}	$V_{CE}=-5V, I_C=-1mA$	200		-0.3	
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-100mA, I_B=-10mA$			-1	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-100mA, I_B=-10mA$				V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$ $f=30MHz$	150			MHz

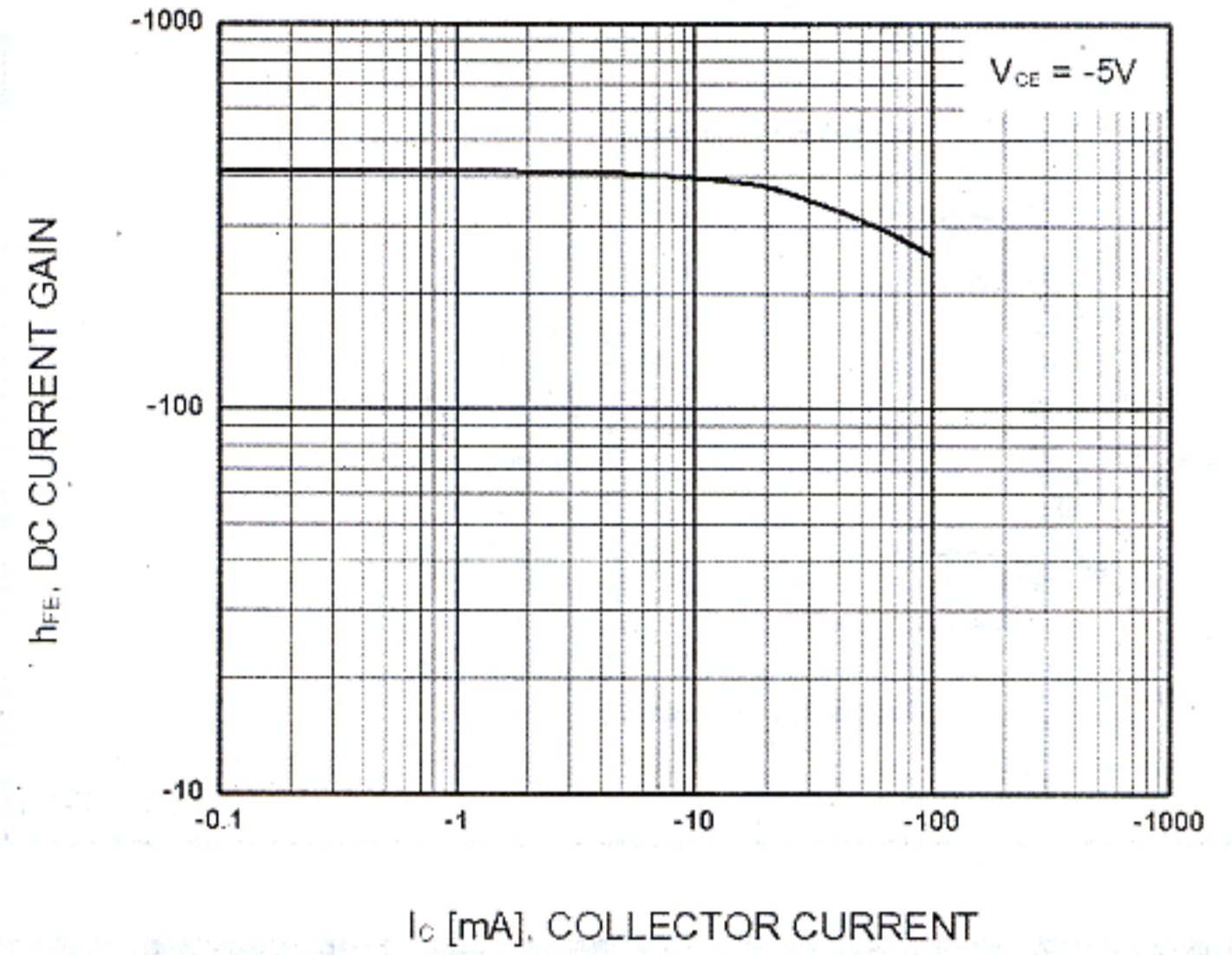
CLASSIFICATION OF h_{FE}

Rank	L	H
Range	200-450	450-1000

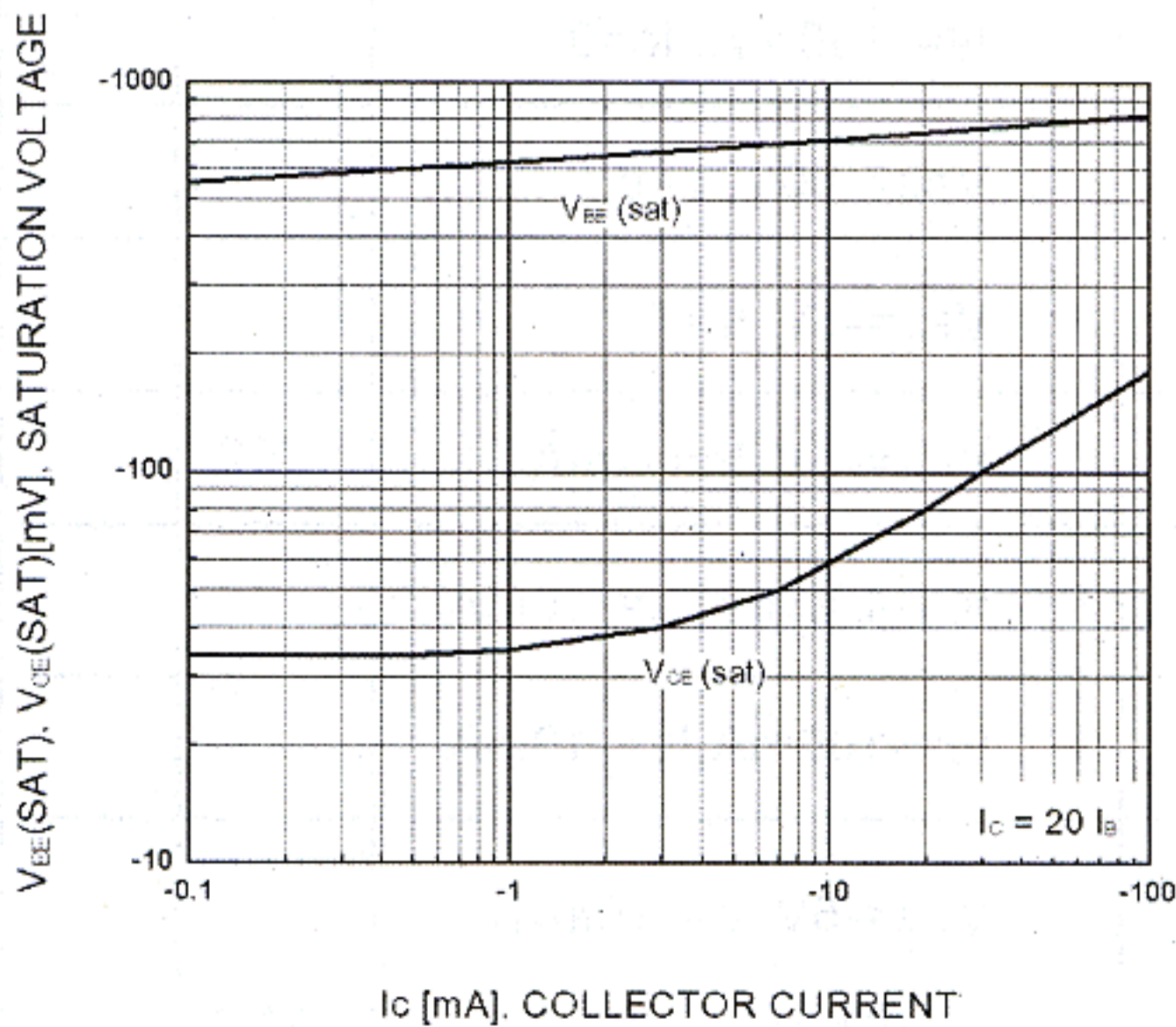
DEVICE MARKING : S9015LT1=M6



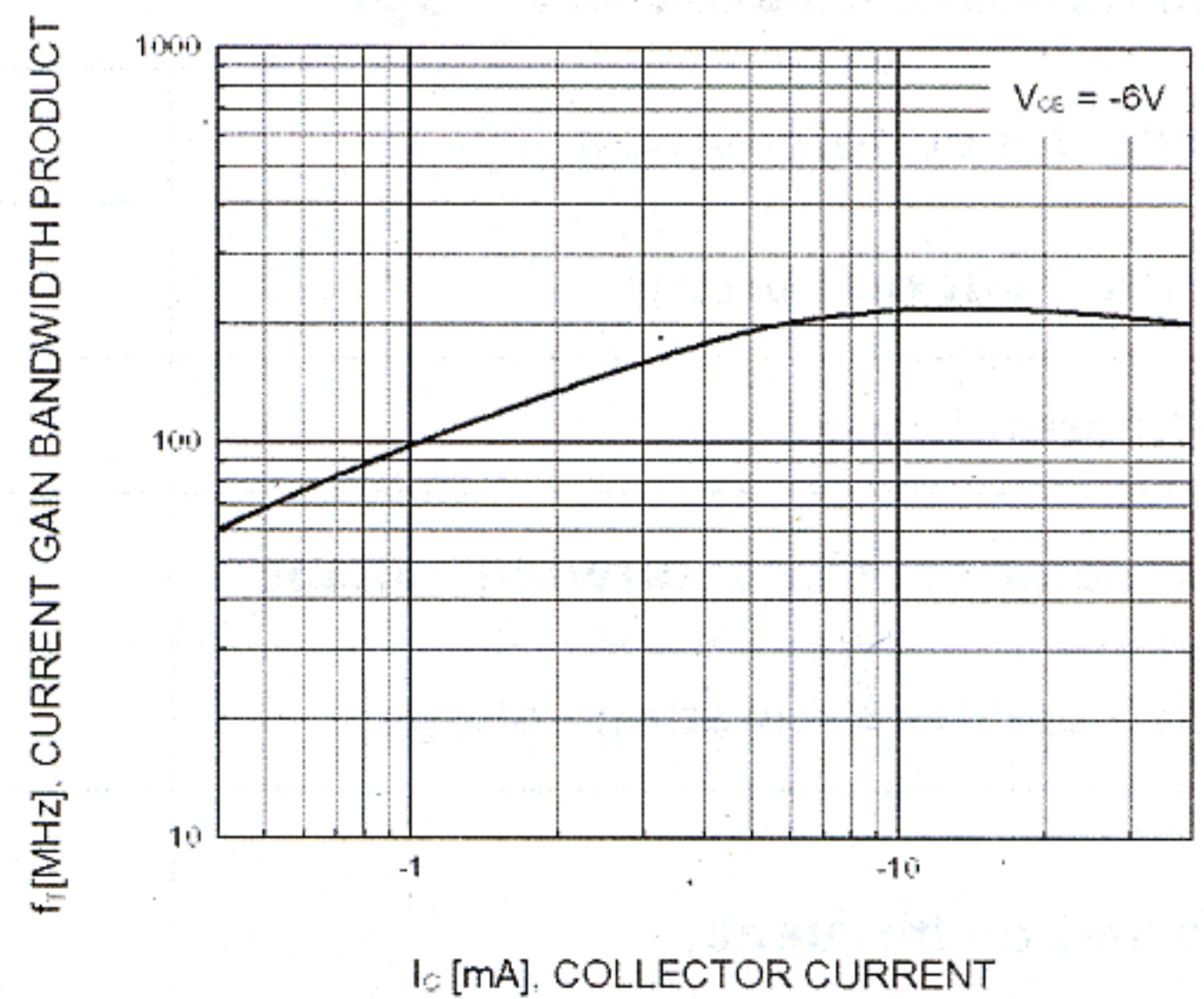
Static Characteristic



DC Current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Current Gain Bandwidth Product